

# **NPN Silicon Epitaxial Planar Transistor**

### **Features**

Low saturation



COMPLIAN



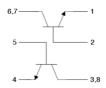
## **Mechanical Data**

• Case: DFN2020-6LC

Molding compound: UL flammability classification rating 94V-0

 Terminals: Tin-plated; solderability, per MIL-STD-202, Method 208 DFN2020-6LC

### **Epuivalent circuit**



| Maximum Ratings & Thermal Characteristics (@ TA = 25°C unless otherwise specified) |                  |            |      |  |  |
|--|------------------|------------|------|--|--|
| Parameter  | Symbol           | Value      | Unit |  |  |
| Collector-Base Voltage   | V <sub>CBO</sub> | 60         | V    |  |  |
| Collector-Emitter Breakdown Voltage  | VCEO             | 60         | V    |  |  |
| Emitter-Base Breakdown Voltage   | V <sub>EBO</sub> | 6          | V    |  |  |
| Collector Current (Continuous)   | Ic               | 1          | А    |  |  |
| Collector Current (Peak)   | Ісм              | 2          | А    |  |  |
| Power Dissipation (TA = 25°C) *1   | PD               | 1.8        | W    |  |  |
| Thermal Resistance Junction-to-Air *1  | R <sub>0JA</sub> | 69         | °C/W |  |  |
| Junction Temperature   | TJ               | -55 ~ +150 | °C   |  |  |
| Storage Temperature Range  | Tstg             | -55 ~ +150 | °C   |  |  |

### Note

1: Per JESD51-7 with 100 mm<sup>2</sup> pad area and 2 oz. Cu (Single-Operation)



| Electrical Characteristics@          | Electrical Characteristics (@ TA = 25°C unless otherwise specified) |   |     |      |      |      |
|--------------------------------------|---|---|-----|------|------|------|
| Parameter                            | Symbol  | Test Condition  | Min | Тур. | Max  | Unit |
| Collector-Base Breakdown Voltage     | V <sub>(BR)CBO</sub>  | Ic = 100μA, I <sub>E</sub> = 0                          | 60  |      |      | V    |
| Collector-Emitter Breakdown Voltage  | V <sub>(BR)CEO</sub>  | I <sub>C</sub> = 10mA, I <sub>B</sub> = 0               | 60  |      |      | V    |
| Emitter-Base Breakdown Voltage       | V <sub>(BR)EBO</sub>  | I <sub>E</sub> = 100μA, I <sub>C</sub> = 0              | 6   |      |      | V    |
| Collector Cut-off Current            | Ісво  | V <sub>CB</sub> = 60V, I <sub>E</sub> = 0               |     |      | 0.1  | μA   |
| Emitter Cut-off Current              | I <sub>EBO</sub>  | V <sub>EB</sub> = 5V, I <sub>C</sub> = 0                |     |      | 0.1  | μA   |
| DC Current Gain                      | hfE   | V <sub>CE</sub> = 2V, I <sub>C</sub> = 100mA            | 150 |      |      |      |
|                                      |   | V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA            | 120 |      |      |      |
|                                      |   | V <sub>CE</sub> = 2V, I <sub>C</sub> = 1A               | 90  |      |      |      |
|                                      |   | V <sub>CE</sub> = 2V, I <sub>C</sub> = 2A               | 35  |      |      |      |
| Collector-emitter Saturation Voltage | V <sub>CE(sat)</sub>  | Ic = 0.5A, I <sub>B</sub> = 0.05A                       |     |      | 0.1  | V    |
|                                      |   | I <sub>C</sub> = 1A, I <sub>B</sub> = 0.05A             |     |      | 0.2  | V    |
|                                      |   | I <sub>C</sub> = 1A, I <sub>B</sub> = 0.1A              |     |      | 0.18 | V    |
| Base-emitter Saturation Voltage      | V <sub>BE(sat)</sub>  | I <sub>C</sub> = 0.5A, I <sub>B</sub> = 0.05A           |     |      | 1    | V    |
|                                      |   | $I_C = 1A, I_B = 0.05A$                                 |     |      | 1    | V    |
|                                      |   | I <sub>C</sub> = 1A, I <sub>B</sub> = 0.1A              |     |      | 1.1  | V    |
| Base-emitter On Voltage              | V <sub>BE(on)</sub>   | I <sub>C</sub> = 0.5A, V <sub>CE</sub> = 2V             |     |      | 0.9  | V    |
| Output Capacity                      | Cob   | V <sub>CB</sub> = 10V, f = 1MHz                         |     | 10   |      | pF   |
| Current-Gain—Bandwidth Product       | f⊤  | I <sub>C</sub> = 0.05A, V <sub>CE</sub> = 2V f = 100MHz |     | 180  |      | MHz  |



# **Ratings and Characteristics Curves**

(@ T<sub>A</sub> = 25°C unless otherwise specified)

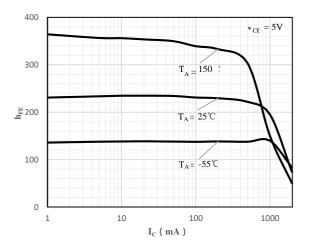


Fig 1 hFE vs. Ic

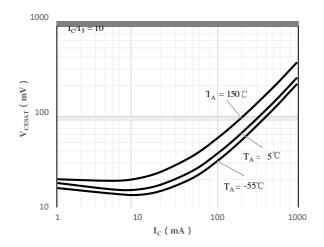


Fig 2 V<sub>CE(sat)</sub> vs. I<sub>C</sub>

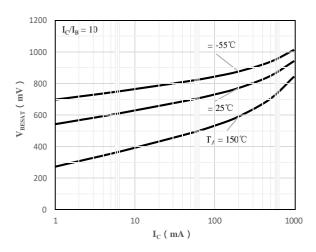


Fig 3 V<sub>BE(sat)</sub> vs. I<sub>C</sub>

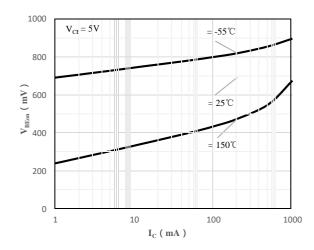
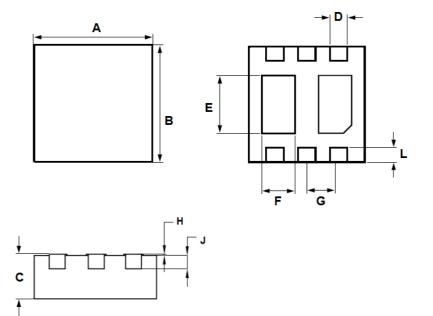


Fig 4 VBE(ON) vs. Ic



# **Package Outline Dimensions**

in inches (millimeters)



| DFN2020-6LC |       |       |  |  |
|-------------|-------|-------|--|--|
| Dimension   | Min.  | Max.  |  |  |
| А           | 1.900 | 2.100 |  |  |
| В           | 1.900 | 2.100 |  |  |
| С           | 0.500 | 0.600 |  |  |
| D           | 0.250 | 0.350 |  |  |
| E           | 0.800 | 1.000 |  |  |
| F           | 0.600 | 0.800 |  |  |
| G           | 0.550 | 0.750 |  |  |
| Н           | 0.000 | 0.050 |  |  |
| J           | 0.103 | 0.303 |  |  |
| L           | 0.174 | 0.326 |  |  |

# **Revision History**

| Document Version | Date of release | Discroption of changes |
|------------------|-----------------|------------------------|
| Rev.A            | 2020.03.04      | First issue            |
|                  |                 |                        |
|                  |                 |                        |



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